



Product Overview

2N5886: 25 A, 80 V NPN Bipolar Power Transistor

For complete documentation, see the data sheet

Product Description

The Power 25A 80 V Bipolar NPN Transistor is designed for general-purpose power amplifier and switching applications.

Features

- Low Collector-Emitter Saturation Voltage  
 $V_{CE(sat)} = 1.0\text{ Vdc}$ , (max) at  $I_C = 15\text{ Adc}$
- Low Leakage Current  
 $I_{CEX} = 1.0\text{ mAdc}$  (max) at Rated Voltage
- Excellent DC Current Gain  
 $h_{FE} = 20$  (min) at  $I_C = 10\text{ Adc}$
- High Current Gain Bandwidth Product  
 $f_t = 4.0\text{ MHz}$  (min) at  $I_C = 1.0\text{ Adc}$
- Pb-Free Packages are Available

Part Electrical Specifications

Product	Compliance	Status	Polarity	$I_C$ Continuous (A)	$V_{(BR)CEO}$ Min (V)	$h_{FE}$ Min	$h_{FE}$ Max	$f_T$ Min (MHz)	$P_{TM}$ Max (W)	Package Type
2N5886G	Pb-free	Active	NPN	25	80	20	100	4	200	TO-204-2

For more information please contact your local sales support at [www.onsemi.com](http://www.onsemi.com)

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